

TSM4433D

20V Dual P-Channel MOSFET



SOP-8

Pin Definition:

1. Source 1 8. Drain 1 2. Gate 1 7. Drain 1 3. Source 2 6. Drain 2 4. Gate 2 5. Drain 2

PRODUCT SUMMARY

V _{DS} (V)	$R_{DS(on)}(m\Omega)$	I _D (A)		
-20	90 @ V _{GS} = -4.5V	-3.9		
	110 @ V _{GS} = -2.5V	-3.2		
	150 @ V _{GS} = -1.8V	-2.6		

Features

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

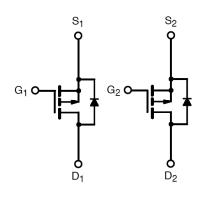
Application

- DC-DC Conversion
- Asynchronous Buck Converter

Ordering Information

Part No.	Package	Packing
TSM4433DCS RL	SOP-8	2.5Kpcs / 13" Reel

Block Diagram



Dual P-Channel MOSFET

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	-20	V
Gate-Source Voltage		V_{GS}	±8	V
Continuous Drain Current, V _{GS} @4.5V.		I _D	-3.9	А
Pulsed Drain Current, V _{GS} @4.5V		I _{DM}	-10	А
Continuous Source Current (Diode Conduction) ^{a,b}		I _S	-1.2	А
Manianum Davida Disabilitation	Ta = 25°C	Б	2.5	107
Maximum Power Dissipation	1.3	W		
Operating Junction Temperature	•	TJ	+150	°C
Operating Junction and Storage Tem	perature Range	T _J , T _{STG}	- 55 to +150	°C

Thermal Performance

Parameter	Symbol	Limit	Unit
Junction to Foot (Drain) Thermal Resistance	R⊖ _{JF}	19	°C/W
Junction to Ambient Thermal Resistance (PCB mounted)	$R\Theta_{JA}$	40	°C/W

1/6

Notes:

- a. Pulse width limited by the Maximum junction temperature
- b. Surface Mounted on FR4 Board, t ≤ 10 sec.

Version: A07



TSM4433D

20V Dual P-Channel MOSFET

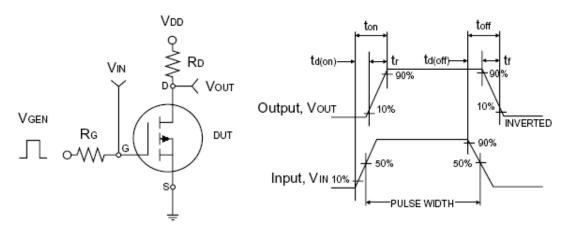


Electrical Specifications

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = -250uA$	BV _{DSS}	-20			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	$V_{GS(TH)}$	-0.45		-0.95	V
Gate Body Leakage	$V_{GS} = \pm 8V, V_{DS} = 0V$	I _{GSS}			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = -16V, V_{GS} = 0V$	I _{DSS}			-1.0	μA
On-State Drain Current ^a	V _{DS} ≤ -5V, V _{GS} = -4.5V	I _{D(ON)}	-6			Α
	$V_{GS} = -4.5V$, $I_D = -3.9A$			75	90	
Drain-Source On-State Resistance ^a	$V_{GS} = -2.5V$, $I_D = -3.2A$	R _{DS(ON)}		90	110	mΩ
	$V_{GS} = -1.8V$, $I_D = -2.6A$			105	150	
Forward Transconductance ^a	$V_{DS} = -5V, I_{D} = -4A$	g _{fs}		6.5		S
Diode Forward Voltage	I _S = -0.9A, V _{GS} = 0V	V_{SD}		- 0.8	-1.2	V
Dynamic ^b						
Total Gate Charge	\/ - 6\/ - 0.0A	Q_g		15.23		
Gate-Source Charge	$V_{GS} = 0V, I_D = -250uA$ $V_{DS} = V_{GS}, I_D = -250\mu A$ $V_{GS} = \pm 8V, V_{DS} = 0V$ $V_{DS} = -16V, V_{GS} = 0V$ $V_{DS} \le -5V, V_{GS} = -4.5V$ $V_{GS} = -4.5V, I_D = -3.9A$ $V_{GS} = -2.5V, I_D = -3.2A$ $V_{GS} = -1.8V, I_D = -2.6A$ $V_{DS} = -5V, I_D = -4A$	Q_{gs}		5.49		nC
Gate-Drain Charge	V _{GS} = -4.5V	Q_{gd}		2.74		
Input Capacitance	\\ - 0\\ \\ - 0\\	C _{iss}		882.51		
Output Capacitance		C _{oss}		145.54		pF
Reverse Transfer Capacitance] I = I.UIVIDZ	C _{rss}		97.26		
Switching ^c						
Turn-On Delay Time	V 0V D 00	t _{d(on)}		17.28		
Turn-On Rise Time	, - ,	t _r		3.73		20
Turn-Off Delay Time	, 52	t _{d(off)}		36.05		nS
Turn-Off Fall Time	NG - 077	t _f		6.19		

Notes:

- a. pulse test: PW ≤300µS, duty cycle ≤2%
- b. For DESIGN AID ONLY, not subject to production testing.
- b. Switching time is essentially independent of operating temperature.



Switching Test Circuit

Switchin Waveforms



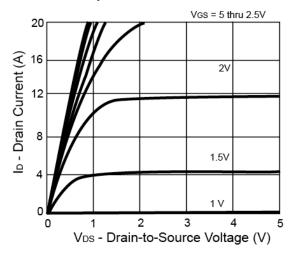




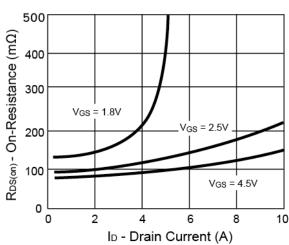
20V Dual P-Channel MOSFET

Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

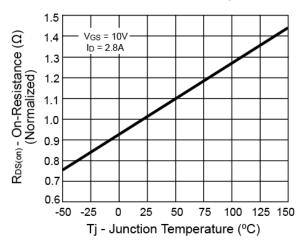
Output Characteristics



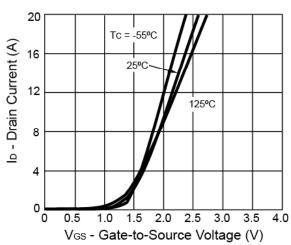
On-Resistance vs. Drain Current



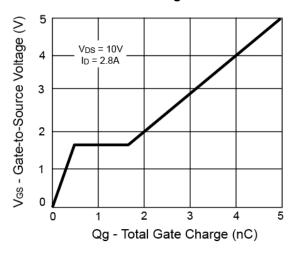
On-Resistance vs. Junction Temperature



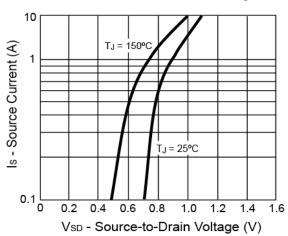
Transfer Characteristics



Gate Charge



Source-Drain Diode Forward Voltage





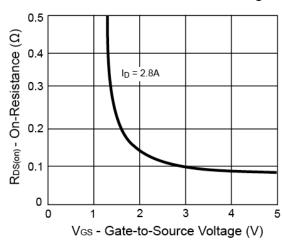


20V Dual P-Channel MOSFET

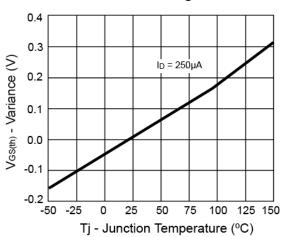


Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

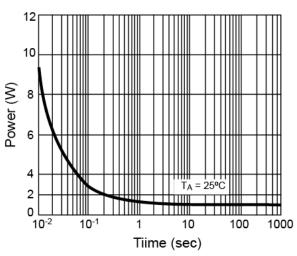
On-Resistance vs. Gate-Source Voltage



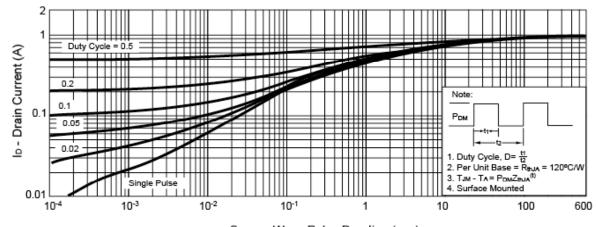
Threshold Voltage



Single Pulse Power



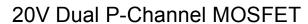
Normalized Thermal Transient Impedance, Junction-to-Ambient



Square Wave Pulse Duration (sec)

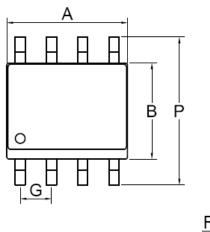


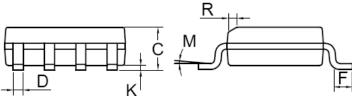
TSM4433D





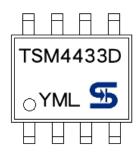
SOP-8 Mechanical Drawing





SOP-8 DIMENSION					
DIM	MILLIMETERS		INCHES		
	MIN	MAX	MIN	MAX.	
Α	4.80	5.00	0.189	0.196	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27	BSC	0.05	BSC	
K	0.10	0.25	0.004	0.009	
М	0°	7°	0°	7°	
Р	5.80	6.20	0.229	0.244	
R	0.25	0.50	0.010	0.019	

Marking Diagram



Y = Year Code

M = Month Code

(A=Jan, B=Feb, C=Mar, D=Apl, E=May, F=Jun, G=Jul, H=Aug,

I=Sep, J=Oct, K=Nov, L=Dec)

5/6

L = Lot Code

Version: A07



TSM4433D 20V Dual P-Channel MOSFET

Notice

Specifications of the products displayed herein are subject to change without notice. TSC or anyone on its behalf, assumes no responsibility or liability for any errors or inaccuracies.

Information contained herein is intended to provide a product description only. No license, express or implied, to any intellectual property rights is granted by this document. Except as provided in TSC's terms and conditions of sale for such products, TSC assumes no liability whatsoever, and disclaims any express or implied warranty, relating to sale and/or use of TSC products including liability or warranties relating to fitness for a particular purpose, merchantability, or infringement of any patent, copyright, or other intellectual property right.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify TSC for any damages resulting from such improper use or sale.